

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	60	V
Gate-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current (Note 6), $V_{GS} = 10\text{V}$	I_D	320	mA
Steady State $T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$		260	
Maximum Continuous Body Diode Forward Current (Note 6)	I_S	0.5	A
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)	I_{DM}	1.2	A

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	260	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	497	$^\circ\text{C/W}$
Steady State			
Total Power Dissipation (Note 6)	P_D	330	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	389	$^\circ\text{C/W}$
Steady State			
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	$V_{GS} = 0\text{V}, I_D = 10\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1.0	μA	$V_{DS} = 60\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.0	1.6	2.5	V	$V_{DS} = 10\text{V}, I_D = 1\text{mA}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	—	2.0	Ω	$V_{GS} = 10\text{V}, I_D = 0.5\text{A}$
						3.0
Forward Transfer Admittance	$ Y_{fs} $	80	—	—	mS	$V_{DS} = 10\text{V}, I_D = 0.2\text{A}$
Diode Forward Voltage	V_{SD}	—	0.75	1.2	V	$V_{GS} = 0\text{V}, I_S = 115\text{mA}$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	30	—	pF	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}$ $f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	4.2	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	2.9	—	pF	
Gate Resistance	R_g	—	133	—	Ω	$f = 1\text{MHz}, V_{GS} = 0\text{V}, V_{DS} = 0\text{V}$
Total Gate Charge	Q_g	—	392	—	pC	$V_{GS} = 4.5\text{V}, V_{DS} = 10\text{V},$ $I_D = 250\text{mA}$
Gate-Source Charge	Q_{gs}	—	157	—	pC	
Gate-Drain Charge	Q_{gd}	—	92	—	pC	
Turn-On Delay Time	$t_{D(ON)}$	—	3.9	—	ns	$V_{DD} = 30\text{V}, V_{GS} = 10\text{V},$ $R_G = 25\Omega, I_D = 200\text{mA}$
Turn-On Rise Time	t_R	—	3.4	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	15.7	—	ns	
Turn-Off Fall Time	t_F	—	9.9	—	ns	

- Notes:
- Device mounted on FR-4 PCB, with minimum recommended pad layout.
 - Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

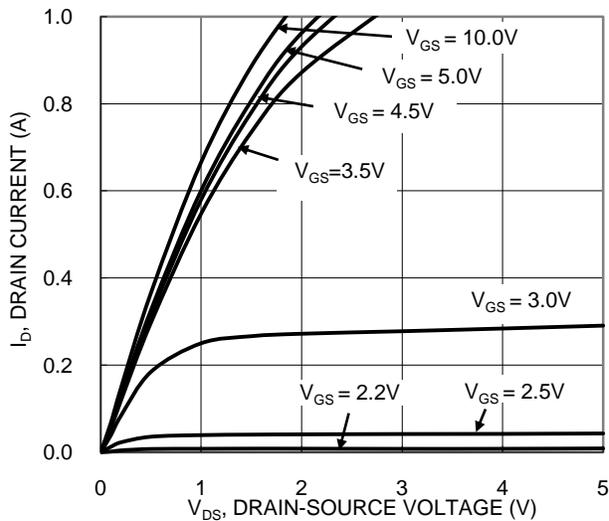


Figure 1. Typical Output Characteristic

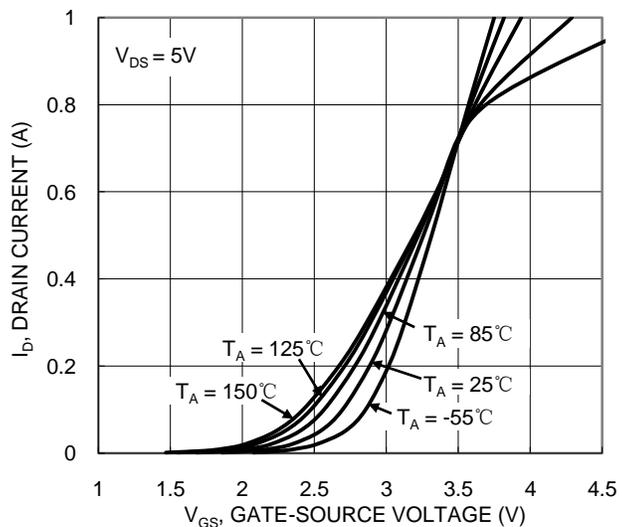


Figure 2. Typical Transfer Characteristic

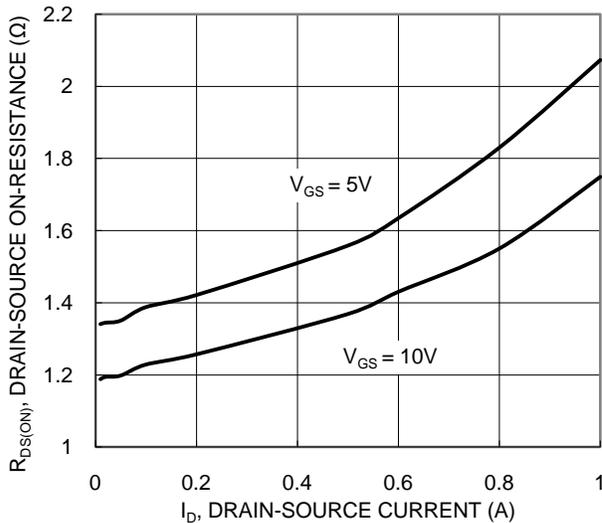


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

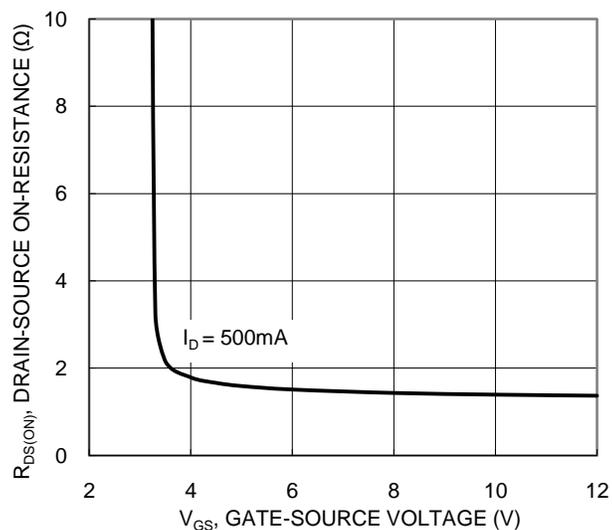


Figure 4. Typical Transfer Characteristic

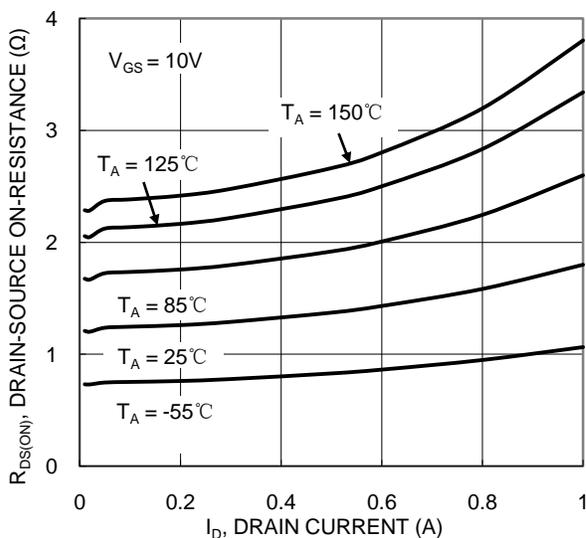


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

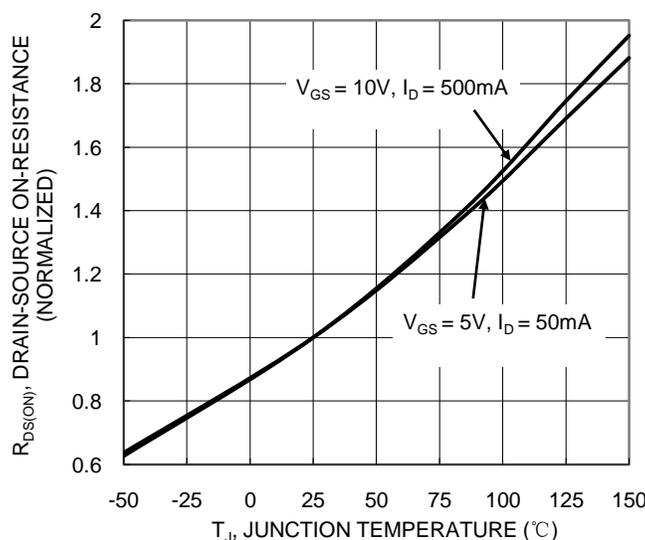


Figure 6. On-Resistance Variation with Junction Temperature

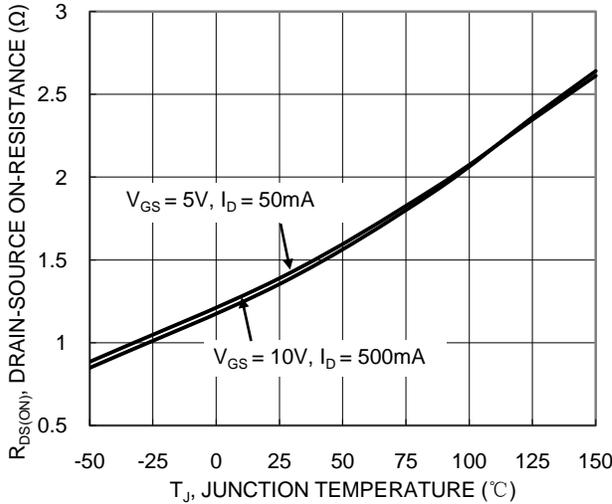


Figure 7. On-Resistance Variation with Junction Temperature

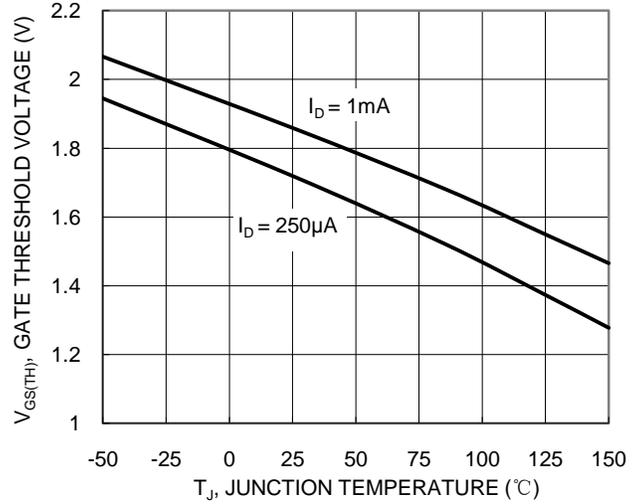


Figure 8. Gate Threshold Variation vs. Junction Temperature

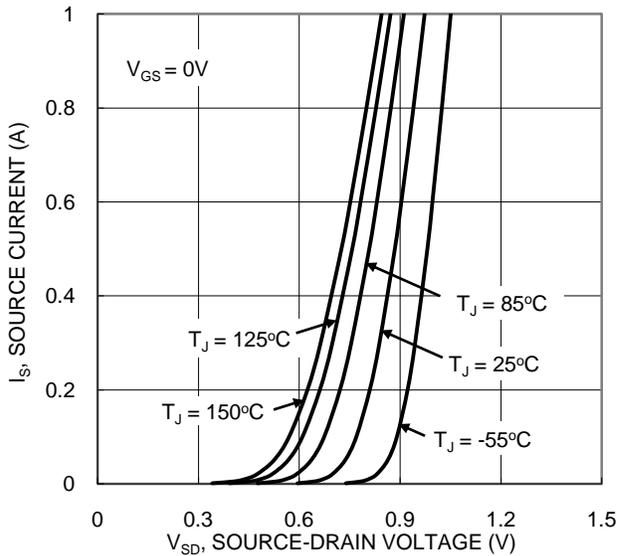


Figure 9. Diode Forward Voltage vs. Current

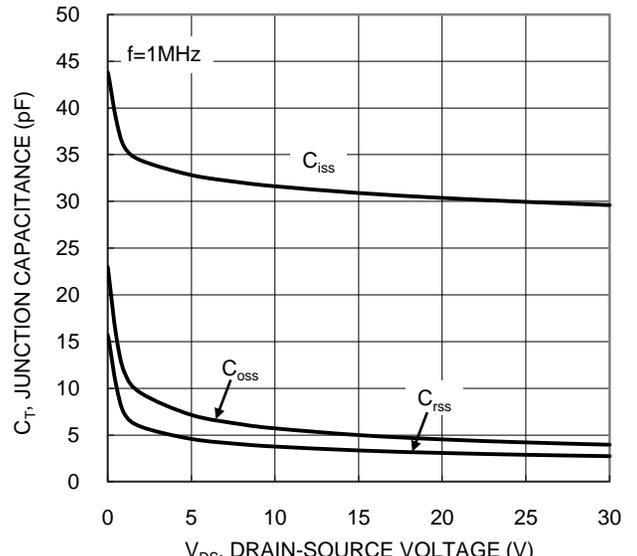


Figure 10. Typical Junction Capacitance

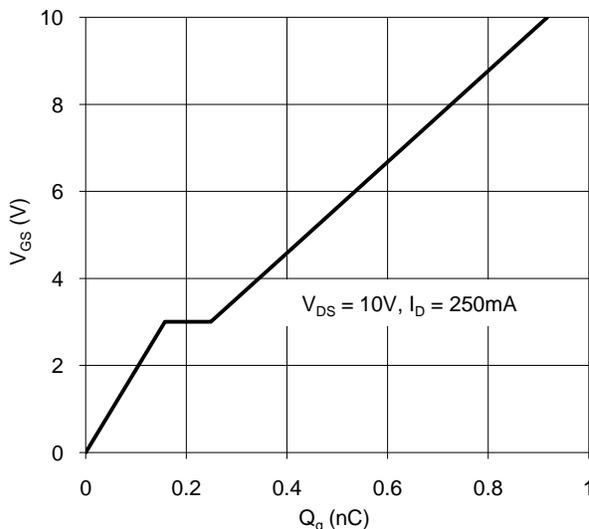


Figure 11. Gate Charge

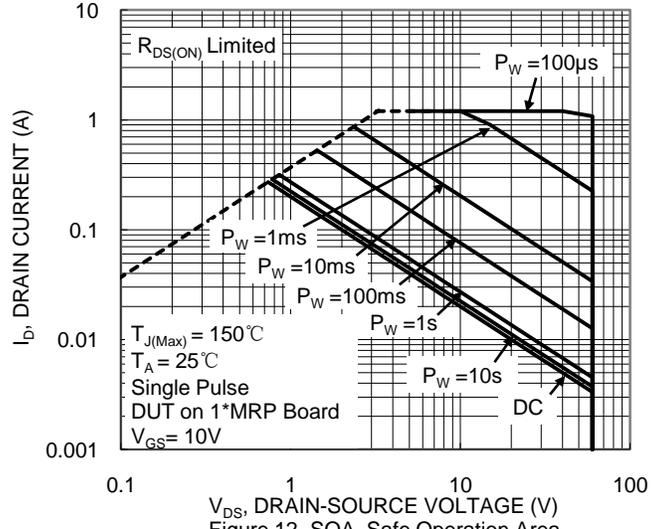


Figure 12. SOA, Safe Operation Area

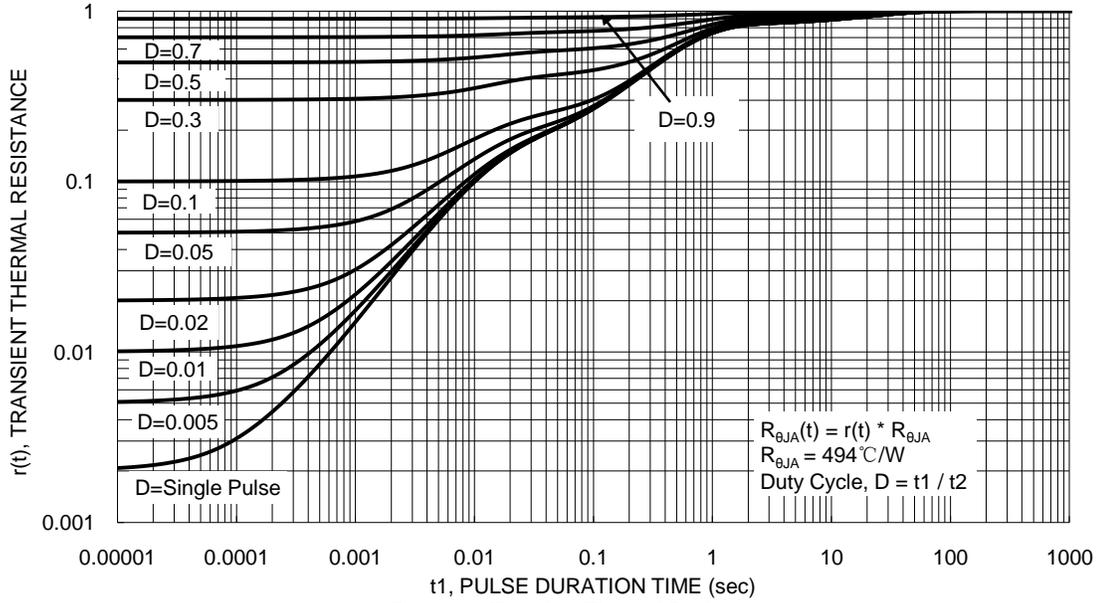
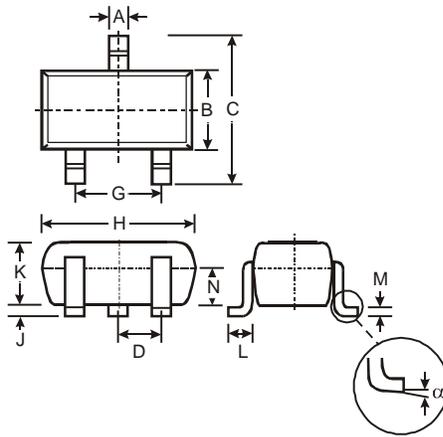


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

SOT523

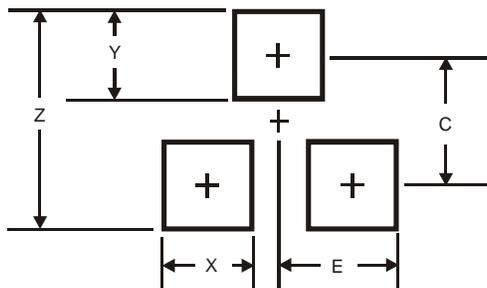


SOT523			
Dim	Min	Max	Typ
A	0.15	0.30	0.22
B	0.75	0.85	0.80
C	1.45	1.75	1.60
D	—	—	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
J	0.00	0.10	0.05
K	0.60	0.80	0.75
L	0.10	0.30	0.22
M	0.10	0.20	0.12
N	0.45	0.65	0.50
α	0°	8°	—
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.

SOT523



Dimensions	Value (in mm)
Z	1.8
X	0.4
Y	0.51
C	1.3
E	0.7

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